

2SK298, 2SK299

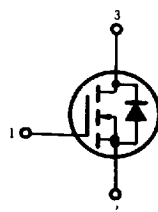
HITACHI/(OPTOELECTRONICS)

SILICON N-CHANNEL MOS FET

HIGH SPEED POWER SWITCHING,
HIGH FREQUENCY POWER AMPLIFIER

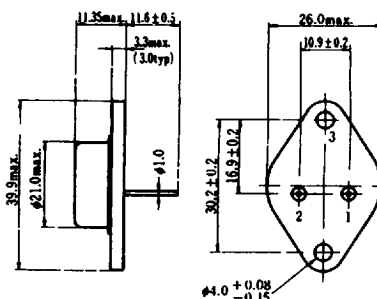
■ FEATURES

- Low On-Resistance.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, RF Amplifiers, and Ultrasonic Power Oscillators.



1. Gate
2. Source
3. Drain (Case)

(Dimensions in mm)



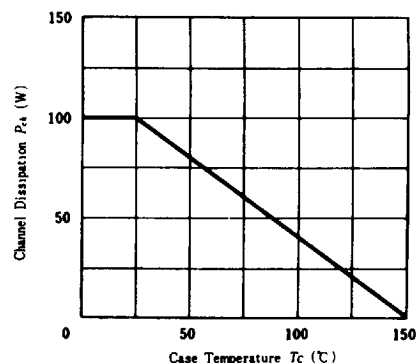
(JEDEC TO-3)

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Item	Symbol	Rating		Unit
		2SK298	2SK299	
Drain-Source Voltage	V_{DS}	400	450	V
Gate-Source Voltage	V_{GS}	± 20		V
Drain Current	I_D	8		A
Drain Peak Current	$I_{D(peak)}$	12		A
Body-Drain Diode Reverse Drain Current	I_{DR}	8		A
Channel Dissipation	P_{ch} *	100		W
Channel Temperature	T_{ch}	150		$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \sim +150$		$^\circ\text{C}$

*Value at $T_c=25^\circ\text{C}$

POWER VS. TEMPERATURE DERATING

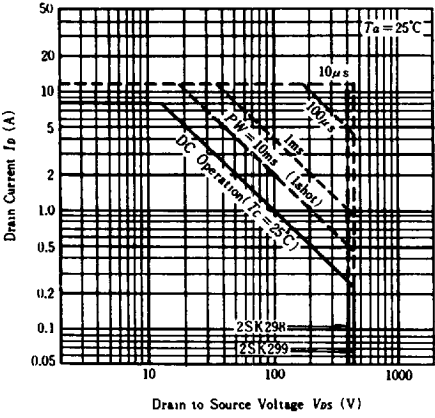


■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

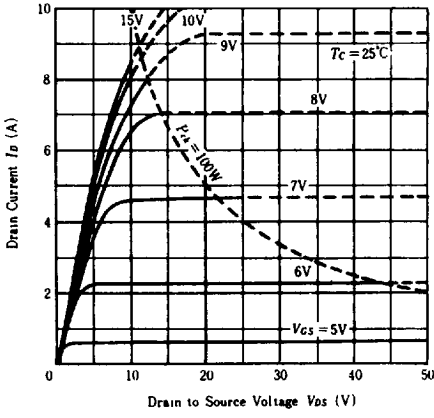
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$I_D=10\text{mA}, V_{GS}=0$	400	—	—	V
			450	—	—	V
Gate-Source Leak Current	I_{GS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$	—	—	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=320\text{V}, V_{GS}=0$	—	—	1	mA
		$V_{DS}=360\text{V}, V_{GS}=0$	—	—	—	—
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$I_D=1\text{mA}, V_{DS}=10\text{V}$	1.0	—	5.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	$I_D=4\text{A}, V_{GS}=15\text{V}^*$	—	1.1	1.75	Ω
Drain-Source Saturation Voltage	$V_{DS(on)}$	$I_D=4\text{A}, V_{GS}=15\text{V}^*$	—	4.4	7.0	V
Forward Transfer Admittance	$ y_{fs} $	$I_D=4\text{A}, V_{DS}=10\text{V}^*$	1.2	1.7	—	S
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0$ $f=1\text{MHz}$	—	800	—	pF
Output Capacitance	C_{oss}		—	180	—	pF
Reverse Transfer Capacitance	C_{rss}		—	20	—	pF
Turn-on Delay Time	t_{don}	$I_D=2\text{A}, V_{GS}=15\text{V}$ $R_L=15\Omega$	—	15	—	ns
Rise Time	t_r		—	35	—	ns
Turn-off Delay Time	t_{doff}		—	85	—	ns
Fall Time	t_f		—	35	—	ns
Body-Drain Diode Forward Voltage	V_{DF}	$I_F=4\text{A}, V_{GS}=0$	—	0.85	—	V
Body-Drain Diode Reverse Recovery Time	t_r	$I_F=4\text{A}, V_{GS}=0$ $di_F/dt=100\text{A}/\mu\text{s}$	—	400	—	ns

*Pulse Test

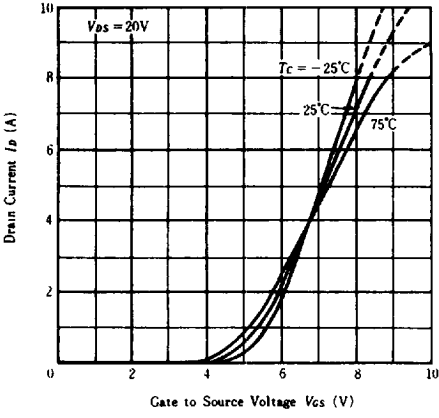
MAXIMUM SAFE OPERATION AREA



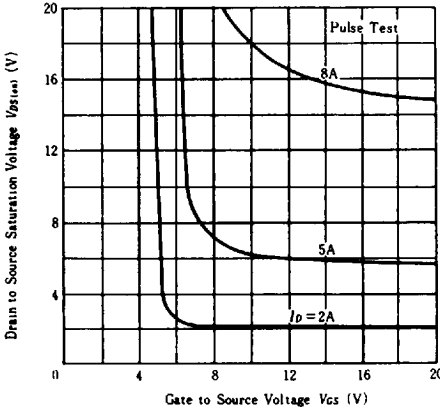
TYPICAL OUTPUT CHARACTERISTICS



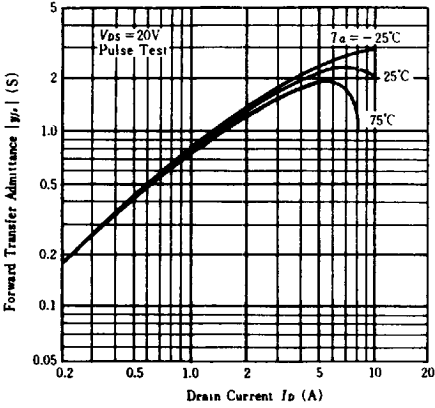
TYPICAL TRANSFER CHARACTERISTICS



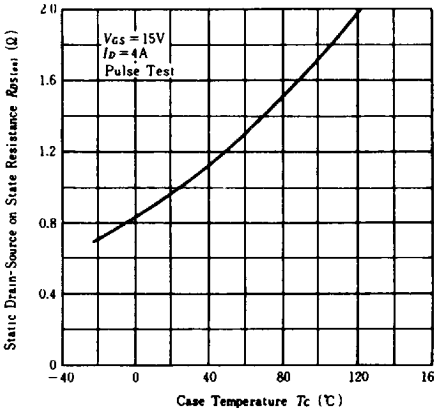
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



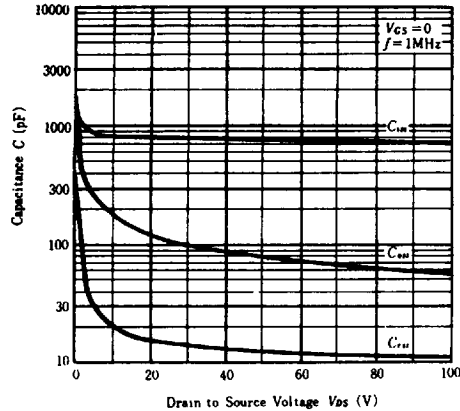
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT



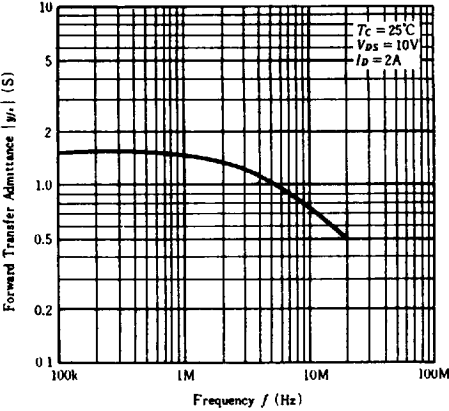
STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE



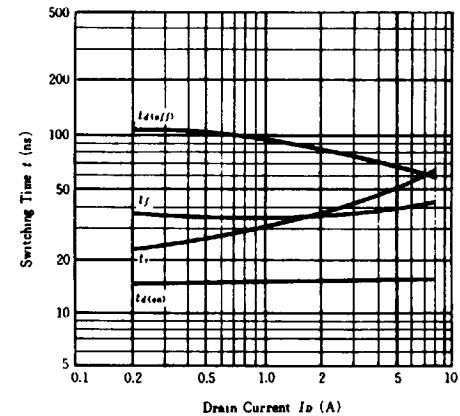
TYPICAL CAPACITANCE VS.
 DRAIN-SOURCE VOLTAGE



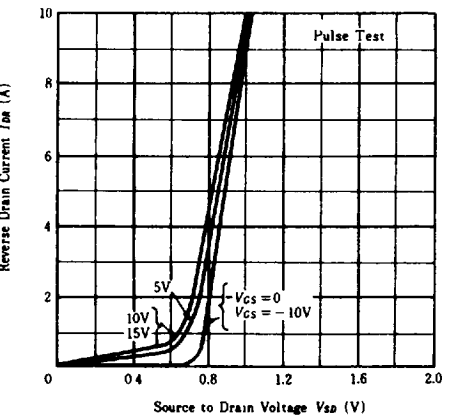
FORWARD TRANSFER ADMITTANCE
 VS. FREQUENCY



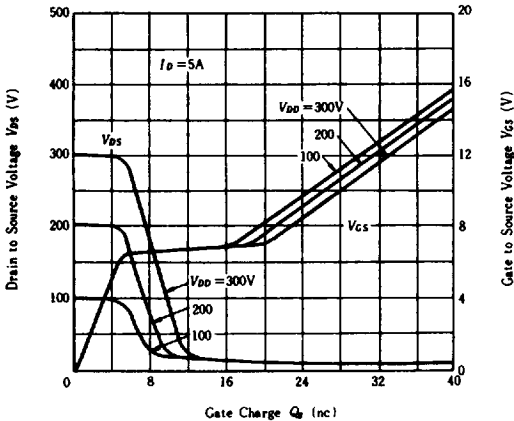
SWITCHING CHARACTERISTICS



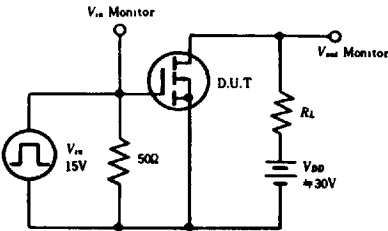
MAXIMUM BODY-DRAIN DIODE
 FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT



WAVEFORMS

